

AMENDMENTS TO THE CLAIMS:

Claims 1-2 (Canceled) Please cancel Claims 1 and 2.

3. (Currently Amended) A semiconductor apparatus, comprising:

a substrate having a transistor formed thereon;

a plurality of first capacitor electrodes secured to said substrate and;

a plurality of second electrodes secured to said substrate and electrically separated
from said first electrodes; and

an insulating film formed so as to cover said first electrodes and which is between the
first electrodes and second electrodes.

wherein the first and second electrodes have a common bottom level and the plurality
of second electrodes each have a top surface which is above a top surface of the first
electrodes;

wherein a distance between a top surface of said substrate and said top surface of the
second electrodes is larger than a distance between the top surface of said substrate and the
top surface of said insulating film.

Claims 4-20. (Canceled) Please cancel Claims 4-20.